

ABSTRACT

There is provided an underlayer coating forming composition for lithography that is used in lithography process of the manufacture of semiconductor devices and that has a high dry etching rate in comparison to photoresists, does not intermix with photoresists, and is capable of flattening the surface of a semi conductor substrate having holes of a high aspect ratio.

The underlayer coating forming composition for lithography comprises, a compound having two or more protected carboxylic groups, a compound having two or more epoxy groups, and a solvent.